

P/N: L-53SYD

SUPER BRIGHT YELLOW

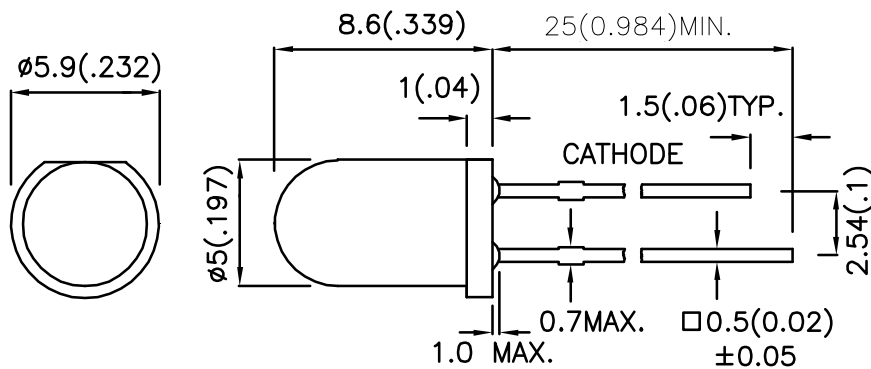
Features

- LOW POWER CONSUMPTION.
- POPULAR T-1 3/4 DIAMETER PACKAGE.
- GENERAL PURPOSE LEADS.
- RELIABLE AND RUGGED.
- LONG LIFE - SOLID STATE RELIABILITY.
- AVAILABLE ON TAPE AND REEL.
- RoHS COMPLIANT.

Description

The Super Bright Yellow device is made with DH InGaAlP (on GaAs substrate) light emitting diode chip.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ " unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.
4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) [2] @ 20mA		Viewing Angle [1]
			Min.	Typ.	2 θ 1/2
L-53SYD	SUPER BRIGHT YELLOW (InGaAlP)	YELLOW DIFFUSED	110	400	60°

Notes:

1. θ 1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.
2. Luminous intensity/ luminous Flux: +/-15%.

Electrical / Optical Characteristics at T_A=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ_{peak}	Peak Wavelength	Super Bright Yellow	590		nm	I _F =20mA
λ_D [1]	Dominant Wavelength	Super Bright Yellow	588		nm	I _F =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Super Bright Yellow	28		nm	I _F =20mA
C	Capacitance	Super Bright Yellow	25		pF	V _F =0V;f=1MHz
V _F [2]	Forward Voltage	Super Bright Yellow	2.0	2.5	V	I _F =20mA
I _R	Reverse Current	Super Bright Yellow		10	uA	V _R = 5V

Notes:

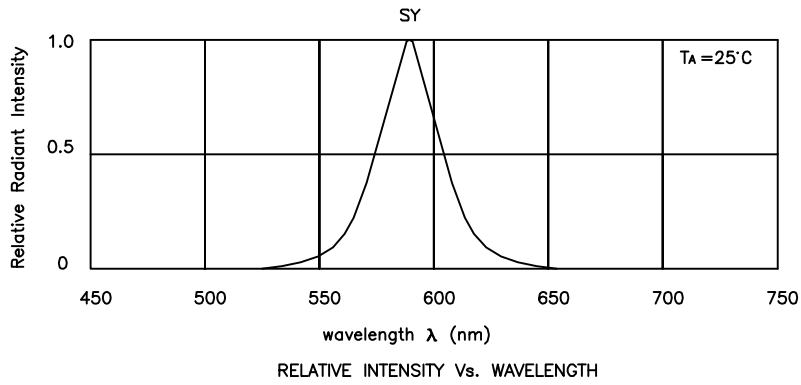
1. Wavelength: +/-1nm.
2. Forward Voltage: +/-0.1V.

Absolute Maximum Ratings at T_A=25°C

Parameter	Super Bright Yellow	Units
Power dissipation	125	mW
DC Forward Current	30	mA
Peak Forward Current [1]	150	mA
Reverse Voltage	5	V
Operating/Storage Temperature	-40°C To +85°C	
Lead Solder Temperature [2]	260°C For 3 Seconds	
Lead Solder Temperature [3]	260°C For 5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 2mm below package base.
3. 5mm below package base.



Super Bright Yellow

L-53SYD

